DISCRETE SEMICONDUCTORS

DATA SHEET

BTA216X series D, E and F Three quadrant triacs guaranteed commutation

Product specification

September 2018



Three quadrant triacs guaranteed commutation

BTA216X series D, E and F

GENERAL DESCRIPTION

Passivated guaranteed commutation triacs in a full pack, plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

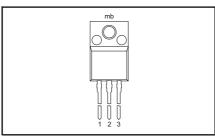
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V	BTA216X- BTA216X- BTA216X- Repetitive peak off-state voltages	600D 600E 600F 600	V
V _{DRM} I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	16 140	A A

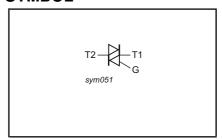
PINNING - SOT186A

PIN	DESCRIPTION		
1	main terminal 1		
2	main terminal 2		
3	gate		
case	isolated		

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages		-	600 ¹	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{hs} ≤ 38 °C	-	16	Α
I _{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge t = 20 ms	-	140	A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after	$ \begin{array}{l} t = 16.7 \text{ ms} \\ t = 10 \text{ ms} \\ I_{TM} = 20 \text{ A}; I_{G} = 0.2 \text{ A}; \\ dI_{G}/dt = 0.2 \text{ A}/\mu\text{s} \end{array} $	-	150 98 100	Α A²s A/μs
$\begin{matrix} I_{GM} \\ P_{GM} \\ P_{G(AV)} \end{matrix}$	triggering Peak gate current Peak gate power Average gate power	over any 20 ms period	- - -	2 5 0.5	A W W
T_{stg}^{stg}	Storage temperature Operating junction temperature	, poriod	-40 -	150 125	ů. Ĉ

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65% ; clean and dustfree	-	-	2500	>
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	full or half cycle with heatsink compound without heatsink compound	1 1		4.0 5.5	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	in free air	-	55	-	K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		BTA216X-		D	Е	F	
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
		T2+ G+	-	5	10	25	mA
		T2+ G- T2- G-	_	5 5 5	10 10	25 25	mA mA
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		3	10	23	
_		T2+ G+	-	15	25	30	mA
		T2+ G-	-	25	30	40	mA
		T2- G-	-	25	30	40	mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	15	25	30	mA
					D, E, F	1	
V _T	On-state voltage	$I_{T} = 20 \text{ A}$	-		1.5		V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$			1.5		V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$	0.25		-		V
I _D	Off-state leakage current	$T_{j} = 125 ^{\circ}\text{C}$ $V_{D} = V_{DRM(max)}; T_{j} = 125 ^{\circ}\text{C}$	-		0.5		mA

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² Device does not trigger in the T2-, G+ quadrant.

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DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		MAX.	UNIT
		BTA216X-	D	Е	F		
dV _D /dt	Critical rate of rise of off-state voltage	V _{DM} = 67% V _{DRM(max)} ; T _j = 110 °C; exponential waveform; gate open circuit	30	60	70	-	V/μs
dl _{com} /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 10 \text{V}/\mu\text{s}; \text{ gate}$ open circuit	2.5	6.2	18	-	A/ms
dI _{com} /dt	Critical rate of change of commutating current	$\begin{array}{l} \text{V}_{\text{DM}} = 400 \text{ V; T}_{\text{j}} = 125 \text{ °C;} \\ \text{I}_{\text{T(RMS)}} = 16 \text{ A;} \\ \text{dV}_{\text{com}}/\text{dt} = 0.1 \text{V/}\mu\text{s; gate} \\ \text{open circuit} \end{array}$	12	20	50	1	A/ms

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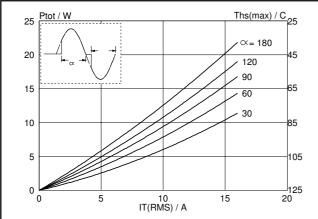


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

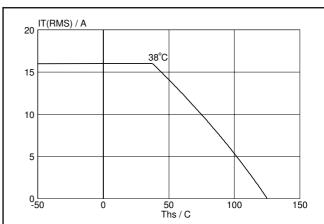


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

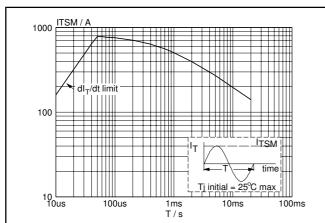


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

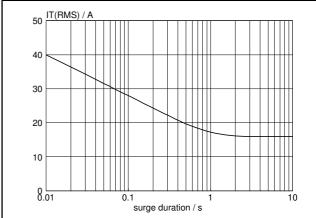


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 38 \, ^{\circ}\text{C}$.

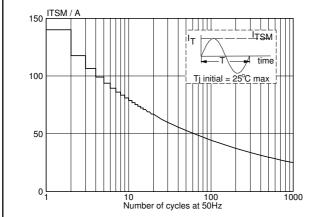


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

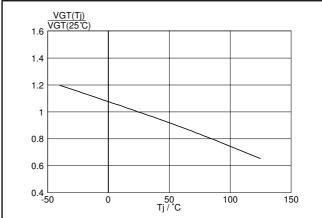
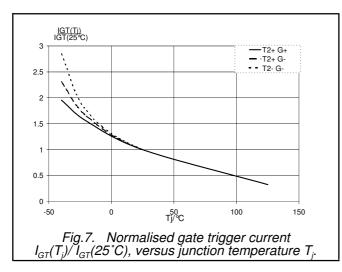
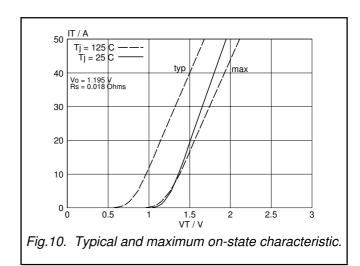


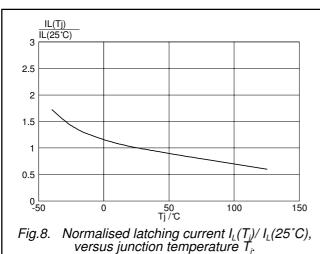
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_{j} .

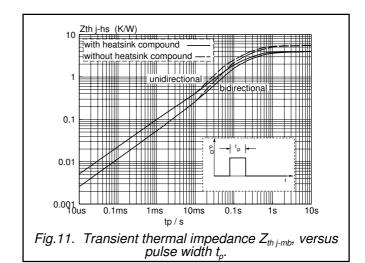
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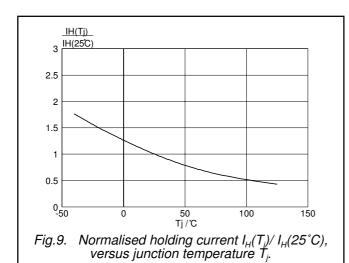
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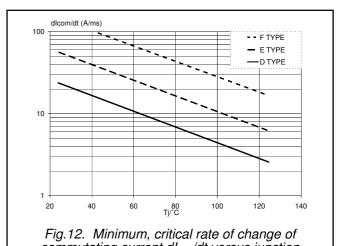
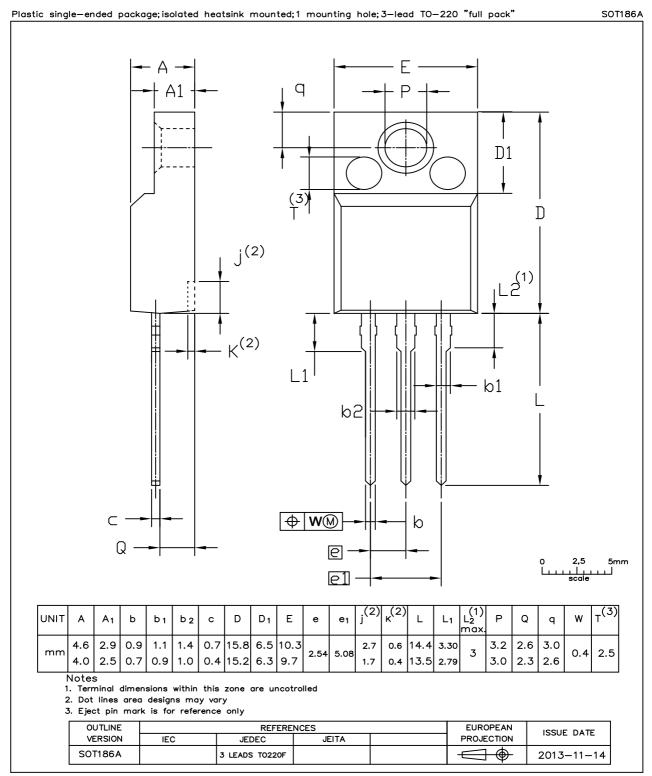


Fig.12. Minimum, critical rate of change of commutating current dI_{com}/dt versus junction temperature, $dV_{com}/dt = 10V/\mu s$.

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MECHANICAL DATA



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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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